

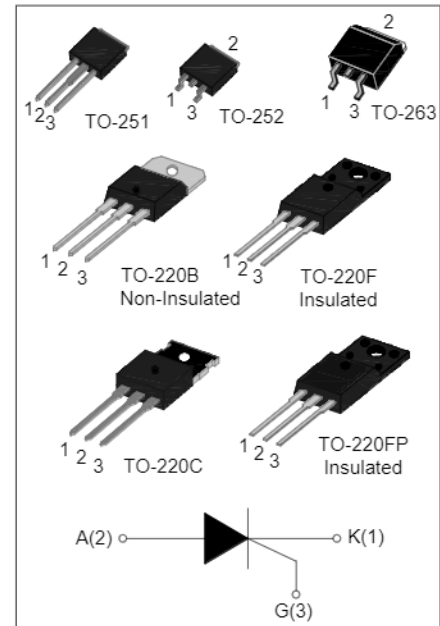


JCT151 Series 12A SCRs

Rev.5.0

DESCRIPTION:

JCT151 series of silicon controlled rectifiers, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. JCT151F/JCT151FP provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).



MAIN FEATURES

Symbol	JCT151-650R	JCT151-800R
V_{DRM}/V_{RRM}	650V	800V
$I_{T(RMS)}$	12A	
I_{GT}	$\leq 15mA$	

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	$^{\circ}C$
Operating junction temperature range		T_j	-40 - 125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)		V_{DRM}	650/800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)		V_{RRM}	650/800	V
RMS on-state current	TO-251/ TO-252 ($T_C=98^{\circ}C$)	$I_{T(RMS)}$	12	A
	TO-220B (Non-Ins)/ TO-220C/ TO-263 ($T_C=100^{\circ}C$)			
	TO-220F (Ins) / TO-220FP(Ins) ($T_C=85^{\circ}C$)			
Non repetitive surge peak on-state current ($t_p=10ms$)		I_{TSM}	120	A

I^2t value for fusing ($t_p=10ms$)	I^2t	72	A^2s
Repetitive rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di_T/dt	50	$A/\mu s$
Peak gate current	I_{GM}	2	A
Peak gate power	P_{GM}	5	W
Average gate power dissipation	$P_{G(AV)}$	0.5	W

ELECTRICAL CHARACTERISTICS ($T_J=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	4	15	mA
V_{GT}		-	0.75	1.5	V
V_{GD}	$V_D=V_{DRM}$ $T_J=125^\circ C$ $R_L=3.3K\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	12	40	mA
I_H	$I_T=500mA$	-	12	30	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_J=125^\circ C$	200	400	-	$V/\mu s$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=23A$ $t_p=380\mu s$	$T_J=25^\circ C$	1.7	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_J=25^\circ C$	10	μA
I_{RRM}		$T_J=125^\circ C$	1	mA

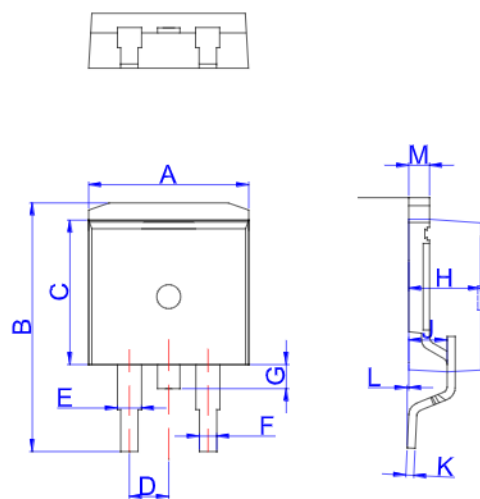
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-mb)}$	Junction to mounting base	TO-251/ TO-252	2.0	$^\circ C/W$
		TO-220B (Non-Ins)/ TO-220C	1.7	
		TO-220F (Ins)/ TO-220FP (Ins)	4.5	
		TO-263	1.5	

ORDERING INFORMATION

	<u>J</u>	<u>CT</u>	<u>151</u>	<u>B</u>	<u>-650R</u>
<u>JieJie Microelectronics Co.,Ltd</u>					650R: $V_{DRM}/V_{RRM} \geq 650V$ 800R: $V_{DRM}/V_{RRM} \geq 800V$
		<u>SCRs</u>			
			<u>$I_{T(RMS)}:12A$</u>		
				H:TO-251 K:TO-252 E:TO-263 F:TO-220F(Ins) FP:TO-220FP(Ins) B:TO-220B(Non-Ins) C:TO-220C	

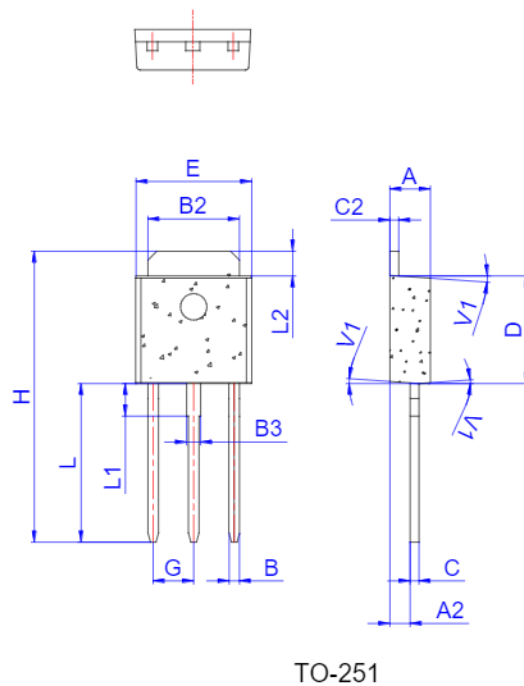
PACKAGE MECHANICAL DATA



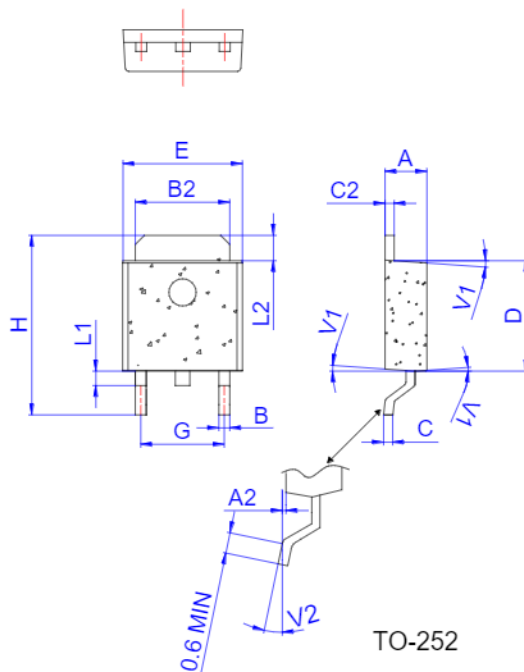
TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

PACKAGE MECHANICAL DATA

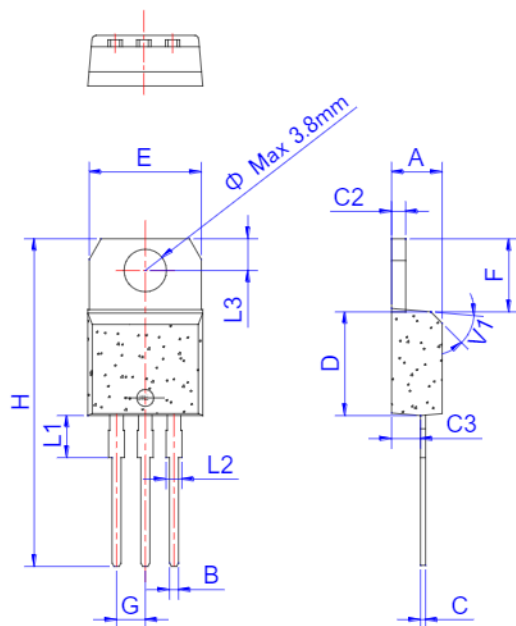


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



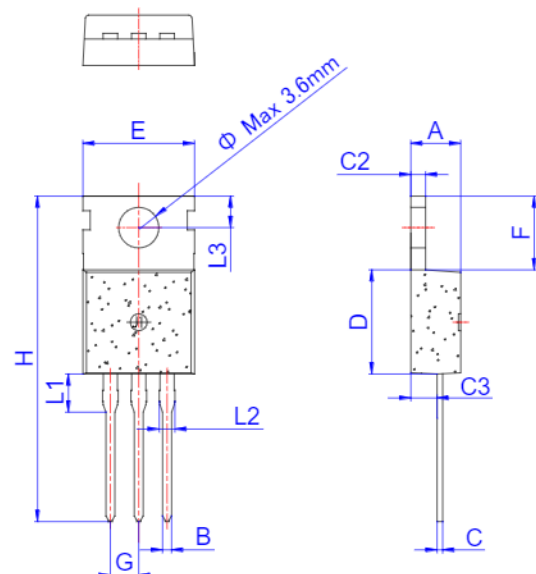
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

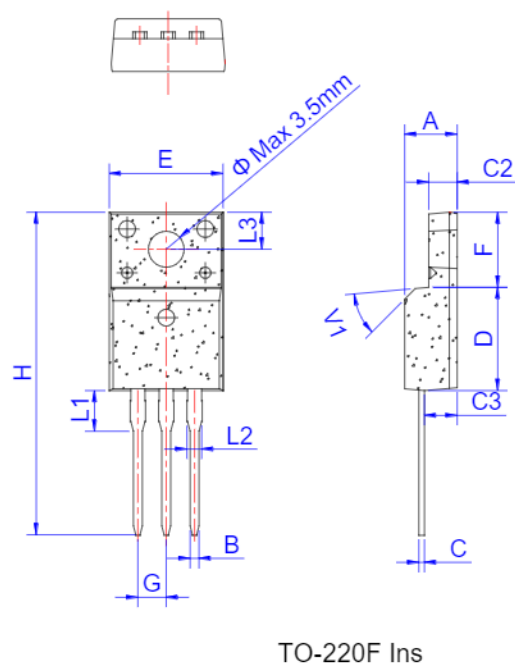
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



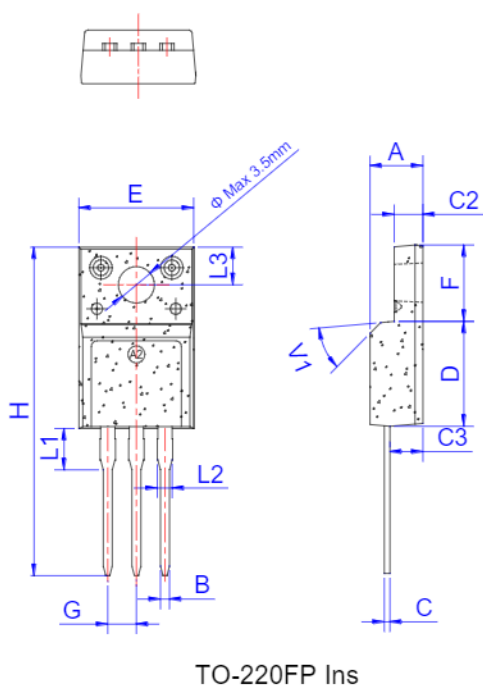
TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

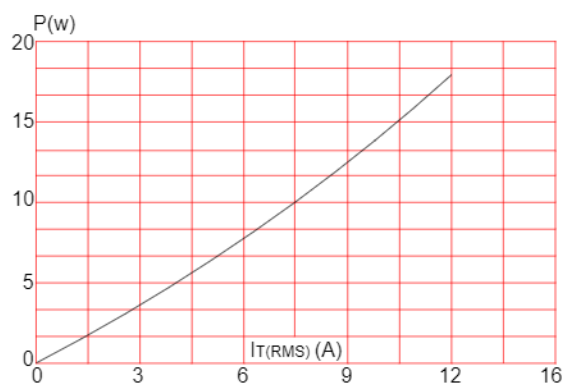
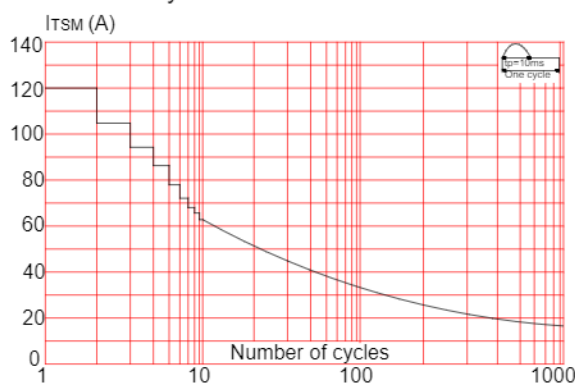
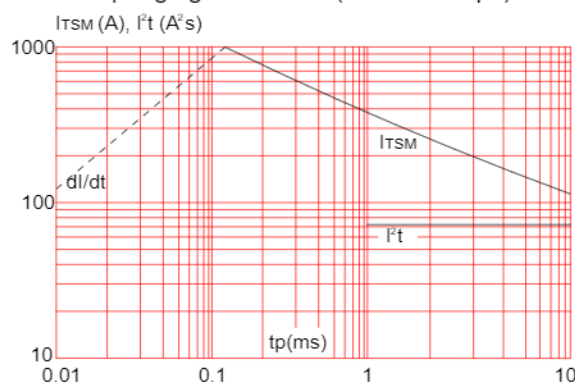
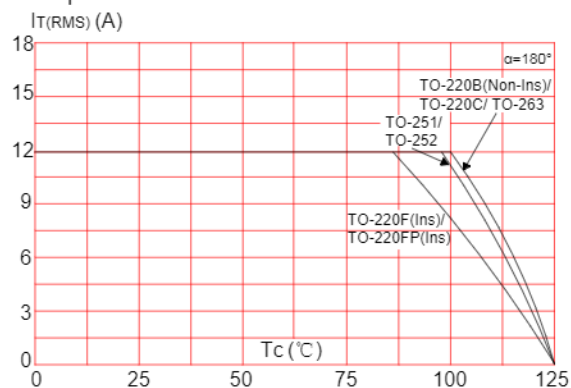
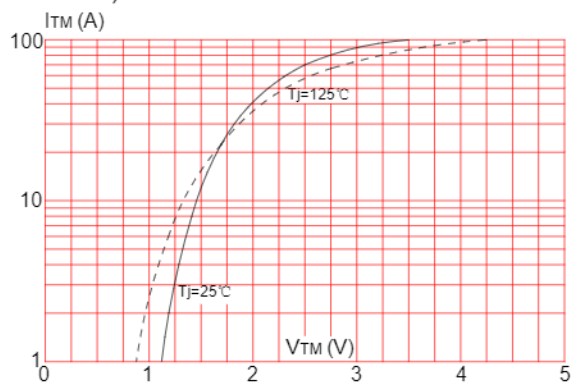
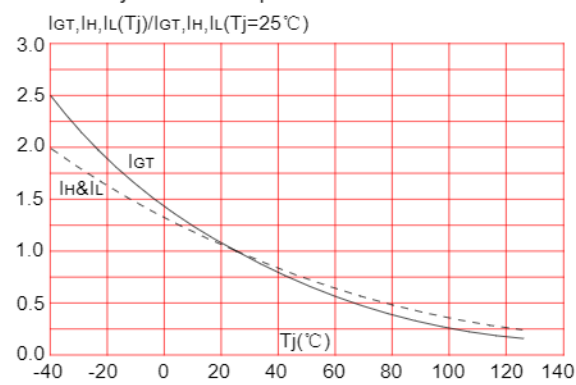
PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristics (maximum values)

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


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